■ NMOS Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V	-	-	1	μA
		V_{DS}=60V, V_{GS}=0V, Tj=150	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ± 20V, V_{DS}=0V	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1	1.5	2.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	-	23	30	mΩ
		V_{GS}				

■ NMOS Typical Electrical and Thermal Characteristics Diagrams

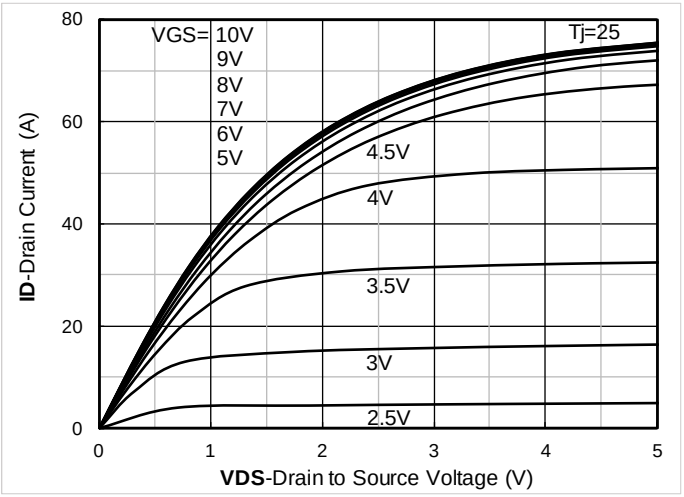

Figure 1. Output Characteristics

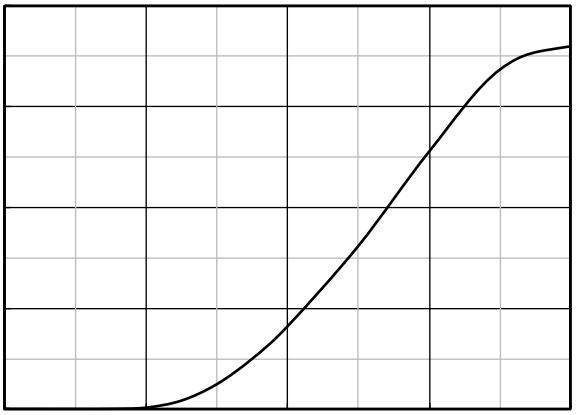

Figure 2. Transfer Characteristics

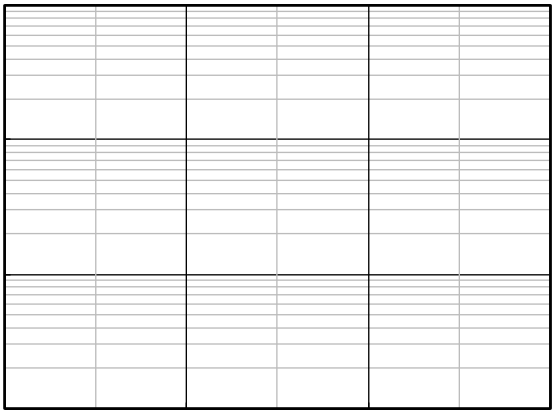

Figure 3. Capacitance Characteristics

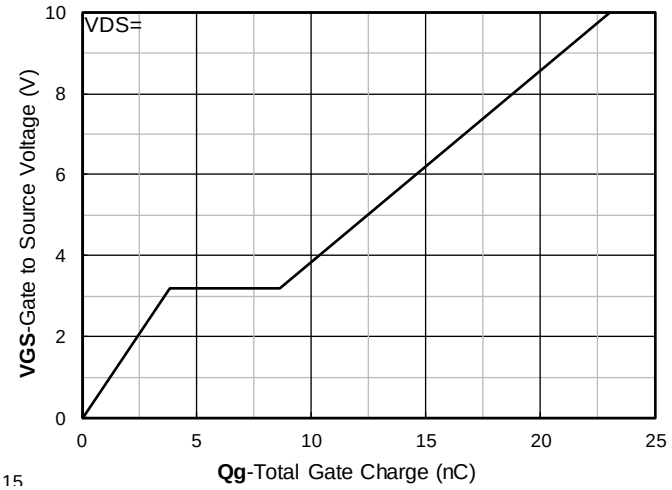

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Figure 4. Gate Charge

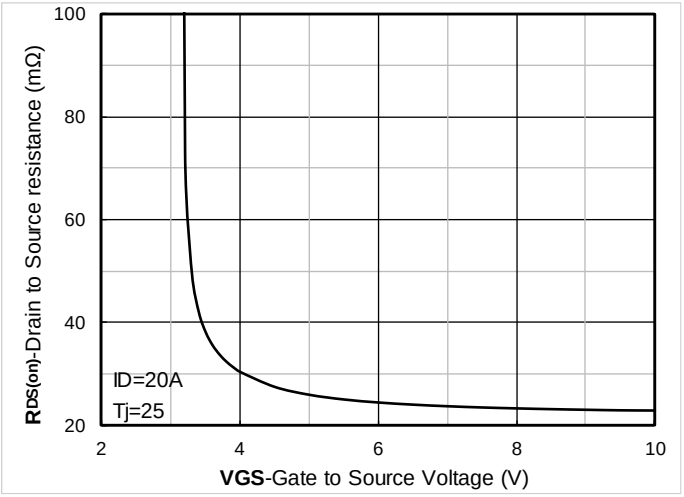


Figure 5. On-Resistance vs Gate to Source Voltage

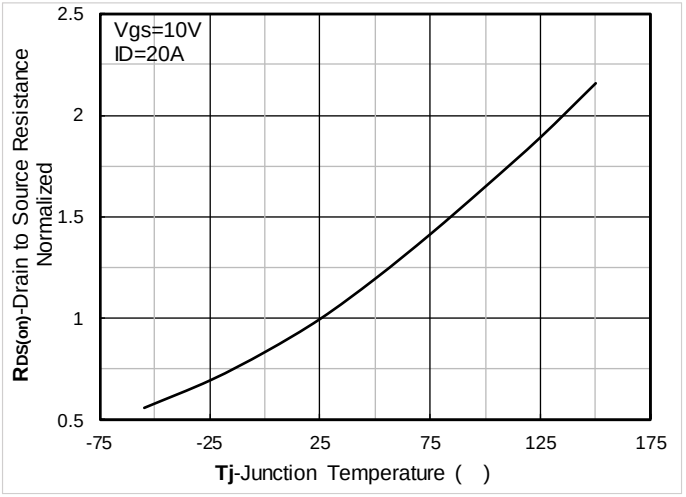


Figure 6. Normalized On-Resistan

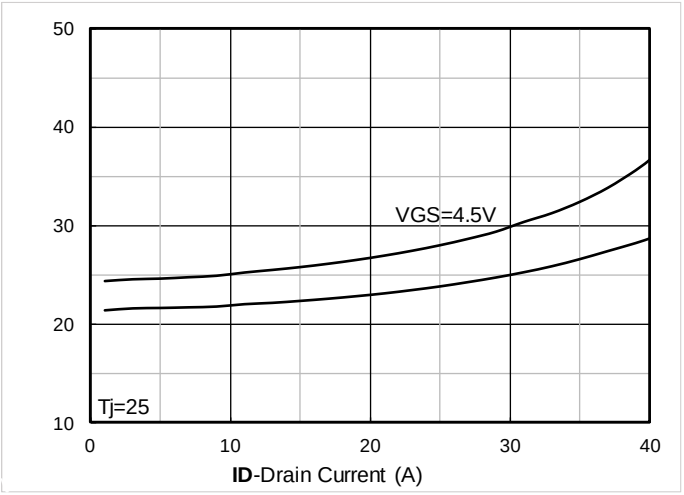


Figure 7. $R_{DS(on)}$ VS Drain Current

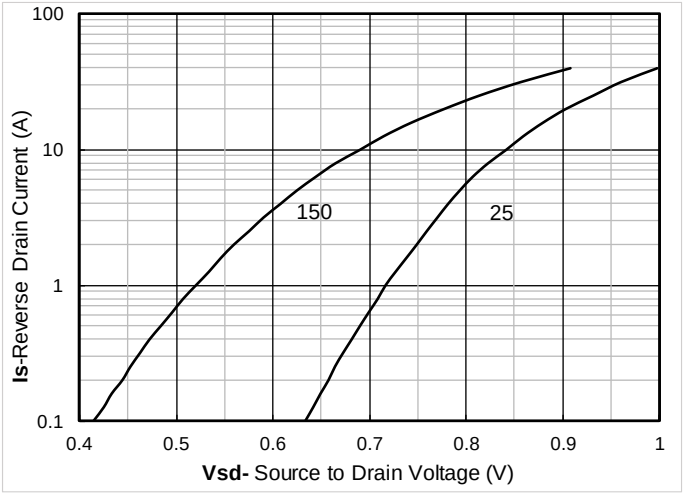


Figure 8. Forward characteristics of reverse diode

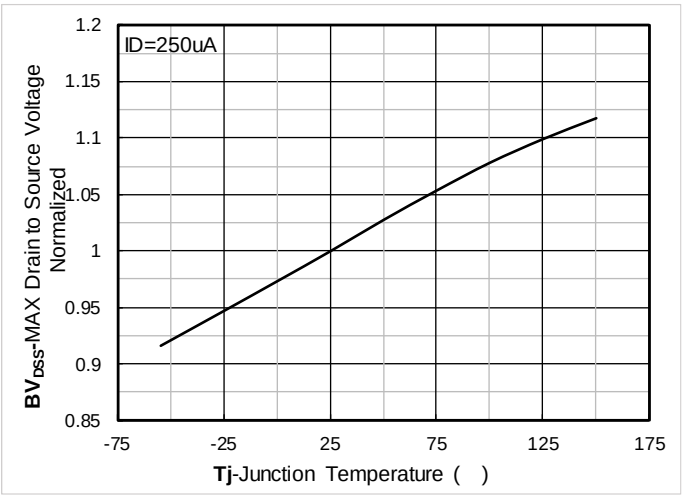


Figure 9. Normalized breakdown voltage

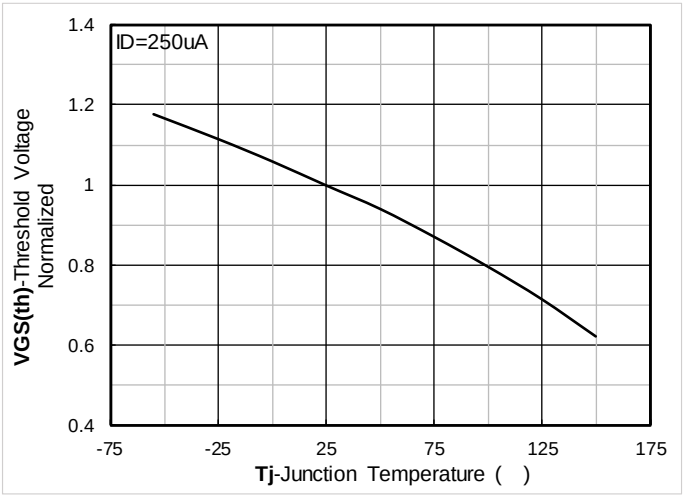
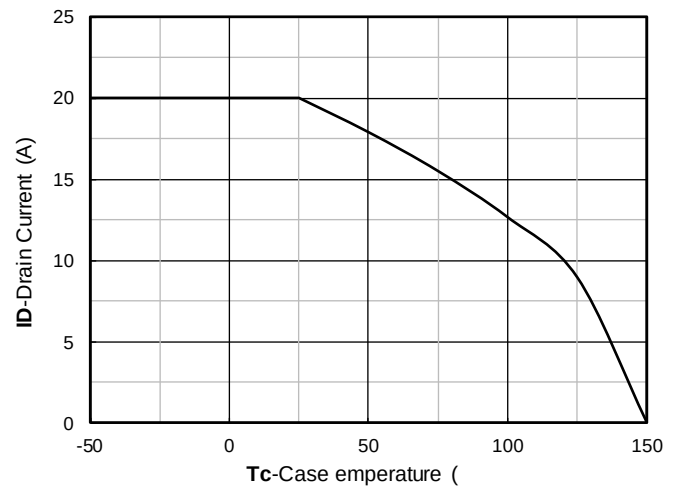


Figure 10. Normalized Threshold voltage



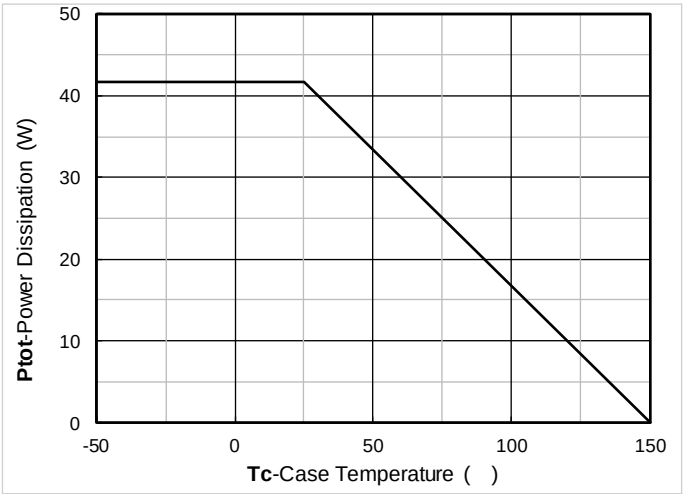
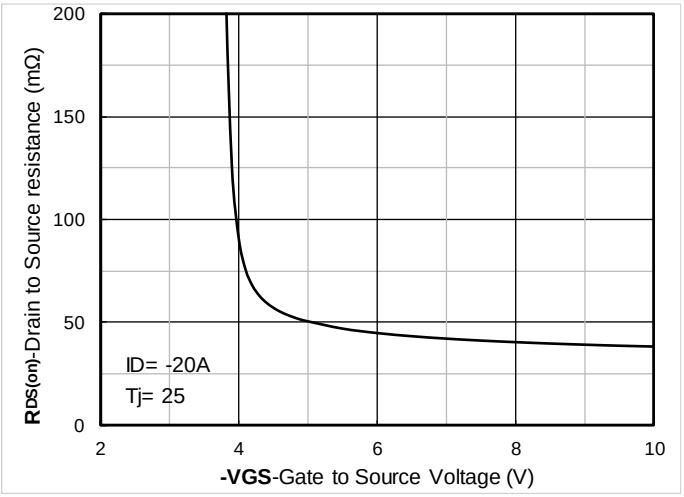


Figure 11. Current dissipation



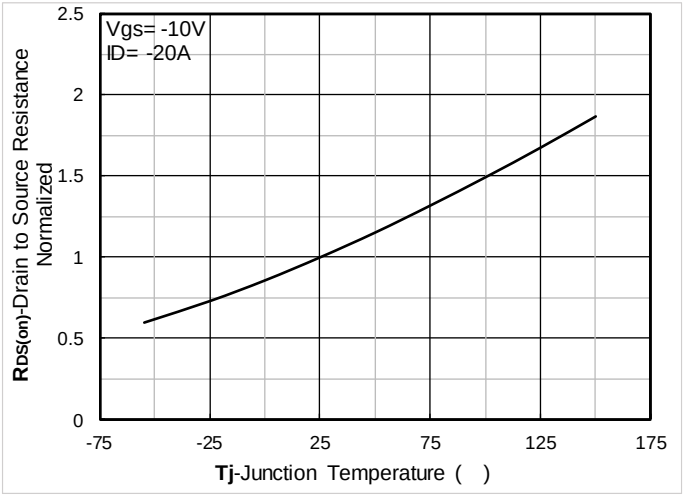


Figure 5. On-Resistance vs Gate to Source Voltage Fiistance vs

en.00000037047 2.5632 306.6357.531.4 8Figu

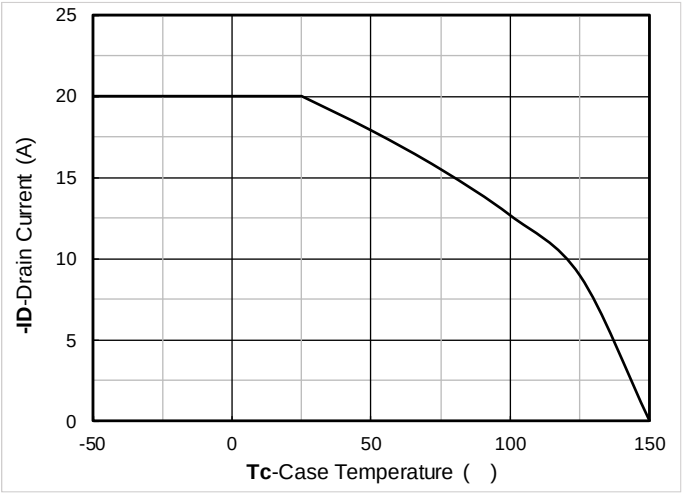


Figure 11. Current dissipation

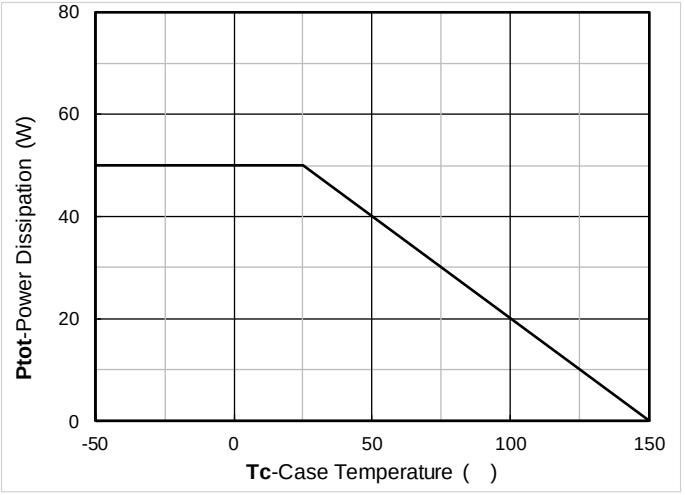


Figure 12. Power dissipation

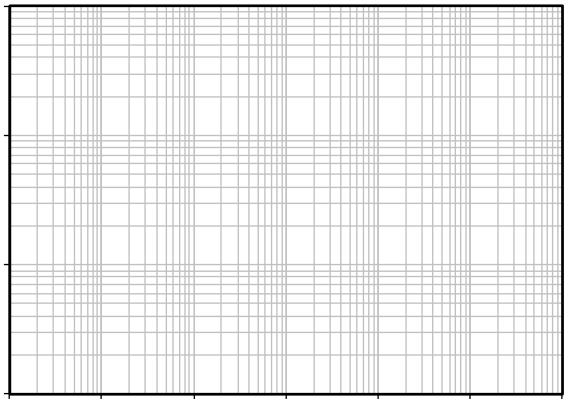


Figure 13. Maximum Transient Thermal Impedance

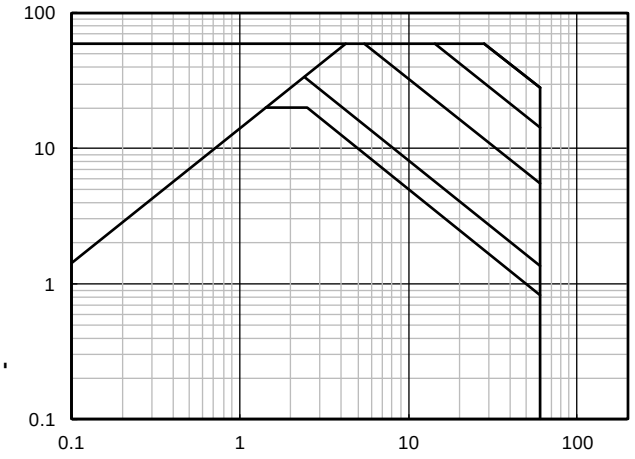


Figure 14. Safe Operation Area

■ **PDFN5060-8L-E-1.1MM**

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